

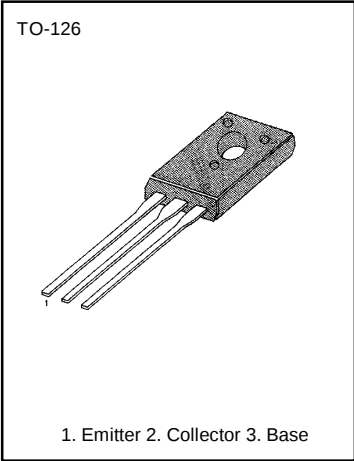
KSE350

PNP EPITAXIAL SILICON TRANSISTOR

**HIGH COLLECTOR-EMITTER
SUSTAINING VOLTAGE
HIGH VOLTAGE GENERAL PURPOSE
APPLICATIONS
SUITABLE FOR TRANSFORMER**
Complement to KSE340

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector- Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter- Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Collector Dissipation ($T_c=25^{\circ}C$)	P_C	20	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-65 ~ 150	$^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}C$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = -1mA, I_B = 0$	-300		V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -300V, I_E = 0$		-100	μA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = -3V, I_C = 0$		-100	μA
DC Current Gain	h_{FE}	$V_{CE} = -10V, I_C = -50mA$	30	240	



